Full power in half the footprint

First bipolar transistors in LFPAK/Power-SO8

These high-power bipolar transistors, housed in LFPAK56 (Power-SO8) packages, deliver DPAK-like thermal and electrical performance in just half the footprint. Offering reliable, energy-efficient performance, they are AEC-Q101 qualified and support high-temperature operation (175 °C).



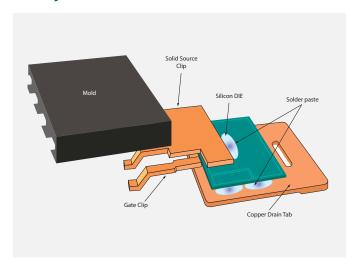
Features and benefits

- 25 types up to 100 V and 15 A in single and double configurations
- High power dissipation (P_{tot})
- > Suitable for high-temperature applications (175 °C)
- Space-saving 5 x 6 mm package outline is half the size of equivalent transistors in DPAK, SOT223, and other packages
- > Low profile (1 mm)
- High reliability and mechanical ruggedness thanks to solidcopper clip (no wires)
- > High energy efficiency due to less heat generation
- > AEC-Q101 qualified
- > Future-proof, growing portfolio

Applications

-) Power management
- Motor drives
- Loadswitches
- > Linear mode voltage regulators
- > LED backlighting applications
- > LED lighting
- Relay replacement

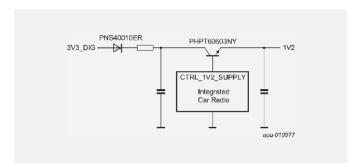
Cutaway view of LFPAK56



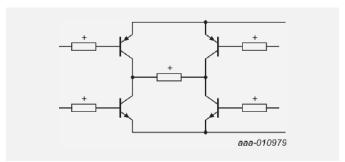


Application examples

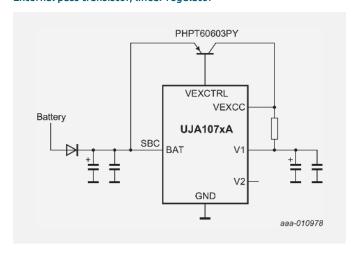
Car radio (PHPT60603NY) External pass transistor, linear regulator



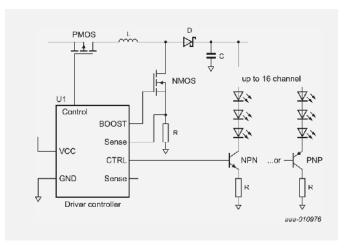
Motor drive (2x PHPT60603NY/PY) or a double LFPAK56D (PHPT610030NK/PK)



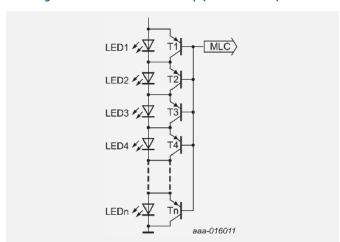
IVN – System Basis Chip (PHPT60603PY) External pass transistor, linear regulator



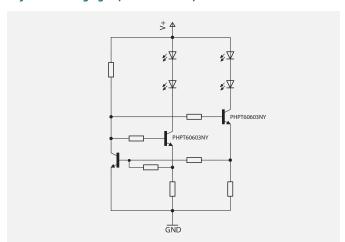
Backlight unit (PHPT61002NYC/PYC)



Dimming transistor in matrix headlamp (PHPT60603PY)



Daytime running light (PHPT60603NY)



High power transistors: single

Package										LFPAK56 Power SO8 (SOT669)			
Size (mm)									5 x 6 x 1				
V _{CEO} (V)	I _c (A)	I _{CM} (A)	h _{FE} typ	@ I _c (A)	@ V _{CE} (V)	R_{CESat} typ. (at) $I_{C}/I_{B} = 10$	V _{CESat} typ (mV); I _C = 0.5 A; I _B =0.05 A	V _{CESat} max (mV)	@ I _c (A)	@ I _s (A)	Polarity		
60	3	8	200/400	0.5	2	60	50	270	3	0.3	NPN	PHPT60603NY	
60	3		3 0	200/400	0.5	2	80	70	360	3	0.3	PNP	PHPT60603PY
100	3	8	2 0	150/250	0.5	10	75	50	330	3	0.3	NPN	PHPT61003NY
			150/250	0.5	10	110	70	360	2	0.2	NPN	PHPT61003PY	
	2	6	150/250	0.5	10	80	50	300	2	0.2	NPN	PHPT61002NYC	
			150/250	0.5	10	125	70	400	2	0.2	PNP	PHPT61002PYC	

High power transistors: double

- Company of the Comp													
											LFPAK56D Power SO8 (SOT1205)		
Package													
Size (mm)										5 x 6 x 1			
V _{CEO} (V)	I _c (A)	I _{CM} (A)	h _{FE} typ	@ I _c (A)	@ V _{CE} (V)	R_{CESat} typ. (at) $I_{C}/I_{B} = 10$	V _{CESat} typ (mV); I _C = 0.5 A; I _B =0.05 A	V _{CESat} max (mV)	@ I _c (A)	@ I _B (A)	Polarity	h _{FE} matching	
	3	8	150/250	0.5	10	75	50	330	3	0.3	2xNPN	-	PHPT610030NK
			150/250	0.5	10	75	50	330	3	0.3	2xNPN	0.95	PHPT610035NK
100			150/220	0.5	10	110	70	360	2	0.2	2xPNP	-	PHPT610030PK
			150/220	0.5	10	110	70	360	2	0.2	2xPNP	0.95	PHPT610035PK
				NPN: 150/250	0.5	10	NPN: 75	50	330	3	0.3	NPN/PNP	-
			PNP: 150/220			PNP: 110	70	360	2	0.2	,		

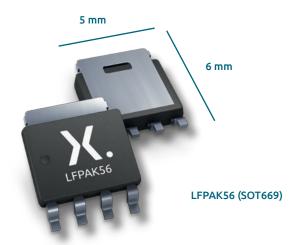
High-current, high power transistors

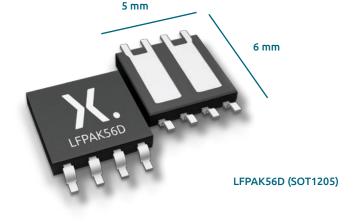
Package								
Size (mm)						5 x 6 x 1		
V _{CEO} (V)	I _c (A)	h _{FE} typ/max	@ I _c (A)	@ V _{CE} (V)	Polarity			
		230/350	0.5	2	NPN	PHPT60406NY		
	6	210/300	0.5	2	PNP	PHPT60406PY		
40	10	230/370	0.5	2	NPN	PHPT60410NY		
40	10	240/350	0.5	2	PNP	PHPT60410PY		
	15	250/410	0.5	2	NPN	PHPT60415NY		
	15	200/340	0.5	2	PNP	PHPT60415PY		
	6	240/390	0.5	2	NPN	PHPT60606NY		
60	6	120/200	0.5	2	PNP	PHPT60606PY		
00	10	210/410	0.5	2	NPN	PHPT60610NY		
	10	120/215	0.5	2	PNP	PHPT60610PY		
	6	140/260	0.5	2	NPN	PHPT61006NY		
100		170/305	0.5	2	PNP	PHPT61006PY		
100	10	150/275	0.5	2	NPN	PHPT61010NY		
	10	180/330	0.5	2	PNP	PHPT61010PY		

LFPAK56 - DPAK comparison

Parameter	LFPAK56	DPAK			
Reliability/mechanical ruggedness	Designed for reliability: solid copper clip, wire-free	Wire bonding prone to breakage			
Outline	5 x 6 mm ²	10 x 7 mm ²			
Height	1 mm	2.3 mm			
Occupied area on PCB	30 mm²	70 mm²			
Max. temperature of complete portfolio	175 °C Image shows result from thermal simulation	150 ℃			

Package details





All package information, including outline and soldering footprint at assets.nexperia.com/documents/outline-drawing/SOT669.pdf

All package information, including outline and soldering footprint at assets.nexperia.com/documents/outline-drawing/SOT1205.pdf



Product Series Page

www.nexperia.com/lfpak-bipolar-transistors

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